

## AMENDMENT

### In the Specification:

Delete the heading at page 1, line 1.

Insert the following heading after the Title.

### BACKGROUND OF THE INVENTION

Amend the heading at page 1, line 5 to read Technical Field of the Invention.

Amend the heading at page 1, line 10 to read Background Description of the Related Art.

Amend the paragraph beginning at page 1, line 23 as follows:

These conventional layout schemes will be explained hereinafter. Fig. 8 shows the common-centroid layout scheme. Fig. 9 shows an equivalent circuit of Fig. 8. M1 and M2 are MOS field effect transistors that are to be matched. The transistor M1 is divided into two sub-transistors MS11 and MS12. Similarly, the transistor M2 is divided into two sub-transistors MS21 and MS22.

Amend the paragraph beginning at page 1, line 28 as follows:

Since these sub-transistors have a common center P as shown in Fig. 8, it is called the common-centroid layout scheme. And gates, drains and sources of the sub-transistors MS11 and MS12 are connected in common to form the transistor M1, as shown in Fig. 9. Similarly, gates, drains and sources of the sub-transistors MS21 and MS22 are connected in common to form the transistor M2.

Replace the heading at page 5, line 11, with the following new heading:

### SUMMARY OF THE INVENTION

Replace the heading at page 5, line 22, with the following new heading:

### BRIEF DESCRIPTION OF THE DRAWINGS

Replace the heading at page 6, line 12, with the following new headings:

### DETAILED DESCRIPTION OF THE INVENTION

Amend the paragraph beginning at page 11, line 4 as follows:

[[A]] The table on the next page below shows formulae to calculate areas for three different layout schemes and the calculated areas for a given set of parameters. Dimensions of the first transistor M1 and the second transistor M2, that are main-transistors, are the width  $W = 80\text{ }\mu\text{m}$  and the length  $L = 10\text{ }\mu\text{m}$  with  $d1 = d2 = d3 = 4\text{ }\mu\text{m}$  for all the layout schemes.